



1. Product profile

1.1 General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- Isolated plastic package
- Low reverse recovery current
- **1.3 Applications**
 - Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Low thermal resistance
- Reduces switching losses in associated MOSFET
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

1.4 Quick reference data

Table 1. Quick reference data

| Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------------------|--|--|--|---|--|
| repetitive peak reverse voltage | | - | - | 600 | V |
| average forward current | square-wave pulse; $\delta = 0.5$; T _h = 47 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> | - | - | 8 | A |
| racteristics | | | | | |
| forward voltage | I _F = 8 A; T _j = 150 °C; see <u>Figure 4</u> | - | 1.5 | 1.85 | V |
| | I _F = 8 A; T _j = 25 °C | - | 2 | 2.9 | V |
| characteristics | | | | | |
| reverse recovery time | I _F = 8 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 25 °C; see <u>Figure 5</u> | - | 20 | - | ns |
| | repetitive peak reverse voltage average forward current racteristics forward voltage characteristics reverse recovery | $\label{eq:current} \begin{array}{l} \mbox{repetitive peak} \\ \mbox{reverse voltage} \\ \mbox{average forward} \\ \mbox{current} & \mbox{square-wave pulse; } \delta = 0.5 \ ; \\ \mbox{T}_h = 47 \ ^\circ C ; \\ \mbox{see Figure 1; see Figure 2} \\ \mbox{racteristics} \\ \mbox{forward voltage} & \mbox{I}_F = 8 \ A ; \ T_j = 150 \ ^\circ C ; \\ \mbox{see Figure 4} \\ \mbox{I}_F = 8 \ A ; \ T_j = 25 \ ^\circ C \\ \mbox{characteristics} \\ \mbox{reverse recovery} & \mbox{I}_F = 8 \ A ; \ V_R = 400 \ V ; \\ \mbox{dl}_F / \mbox{dl} = 500 \ A / \ \mu s; \ T_j = 25 \ ^\circ C ; \\ \end{tabular}$ | $\begin{array}{c} \mbox{repetitive peak} & - & - & - & - & - & - & - & - & - & $ | $\begin{tabular}{lllllllllllllllllllllllllllllllllll$ | $\begin{array}{c} \mbox{repetitive peak} & - & - & 600 \\ \mbox{average forward} & square-wave pulse; \delta = 0.5 ; & - & - & 8 \\ \mbox{current} & T_h = 47 \ ^{\circ}C; & see \ Figure 1; see \ Figure 2 \end{array}$ $\begin{array}{c} \mbox{racteristics} & & & \\ \mbox{forward voltage} & I_F = 8 \ A; \ T_j = 150 \ ^{\circ}C; & - & 1.5 \ 1.85 \\ \ see \ Figure 4 \\ \hline I_F = 8 \ A; \ T_j = 25 \ ^{\circ}C \end{array} & - & 2 \ 2.9 \end{array}$ $\begin{array}{c} \mbox{characteristics} & & \\ \mbox{reverse recovery} & I_F = 8 \ A; \ V_R = 400 \ V; & - \ dI_F/dt = 500 \ A/\mu s; \ T_j = 25 \ ^{\circ}C; \end{array}$ |



2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------------------|--------------------|--------------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | К | cathode | | |
| 2 | А | anode | mb | K — A 001aaa020 |
| mb | n.c. | mounting base; isolated | | |
| | | | SOD113 (TO-220F) | |

3. Ordering information

Table 3.Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BYC8DX-600 | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack" | SOD113 |

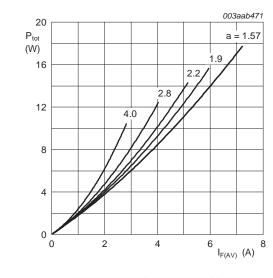
Hyperfast power diode

4. Limiting values

Table 4. Limiting values

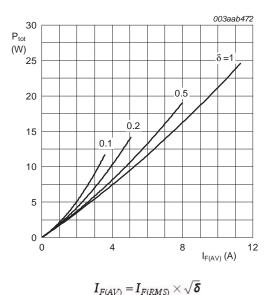
In accordance with the Absolute Maximum Rating System (IEC 60134).

| | | - | | | |
|--------------------|--|--|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Max | Unit |
| V _{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V _{RWM} | crest working reverse voltage | | - | 600 | V |
| V _R | reverse voltage | DC | - | 600 | V |
| I _{F(AV)} | average forward current | square-wave pulse; $\delta = 0.5$; T _h = 47 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> | - | 8 | A |
| I _{FRM} | repetitive peak forward current | square-wave pulse; δ = 0.5 ; t_p = 25 $\mu s;$ T_h = 47 °C | - | 16 | А |
| I _{FSM} | non-repetitive peak forward current | t _p = 10 ms; sine-wave pulse; T _{j(init)} = 25 °C | - | 55 | A |
| | | t _p = 8.3 ms; sine-wave pulse; T _{j(init)} = 25 °C | - | 60 | А |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| Tj | junction temperature | | - | 150 | °C |
| | | | | | |



 $a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$









Hyperfast power diode

5. Thermal characteristics

| Table 5. | Thermal characteristics | | | | | |
|----------------------|--|---------------------------------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-h)} | thermal resistance from | without heatsink compound | - | - | 7.2 | K/W |
| | junction to heatsink | with heatsink compound ; see Figure 3 | - | - | 5.5 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | | - | 60 | - | K/W |

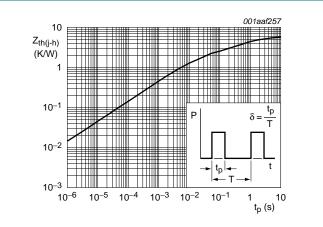


Fig 3. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

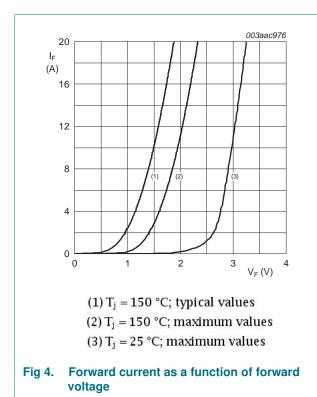
| Table 6. | Isolation characteristics | | | | | |
|------------------------|---------------------------|---|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _{isol(RMS)} | RMS isolation voltage | 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C _{isol} | isolation capacitance | f = 1 MHz ; from cathode to external heatsink | - | 10 | - | pF |

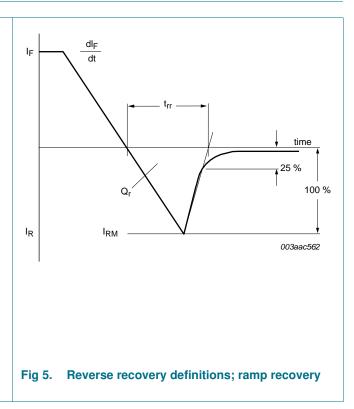
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7. Characteristics

| Table 7. | Characteristics | | | | | |
|-----------------|----------------------------------|---|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _F | forward voltage | I _F = 8 A; T _j = 150 °C; see <u>Figure 4</u> | - | 1.5 | 1.85 | V |
| | | I _F = 8 A; T _j = 25 °C | - | 2 | 2.9 | V |
| I _R | reverse current | $V_{R} = 500 \text{ V}; \text{ T}_{j} = 100 \text{ °C}$ | - | 1.1 | 3 | mA |
| | | V _R = 600 V | - | 9 | 40 | μA |
| Dynamic | characteristics | | | | | |
| Qr | recovered charge | $I_F = 1 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s}$ | - | 13 | - | nC |
| t _{rr} | reverse recovery time | $\label{eq:lf} \begin{array}{l} I_F = 8 \; A; V_R = 400 \; V; dI_F/dt = 500 \; A/\mus; \\ T_j = 100 \; ^\circC \end{array}$ | - | 32 | 40 | ns |
| | | I_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/µs; T_j = 25 °C | - | 30 | 52 | ns |
| | | $\label{eq:least} \begin{array}{l} I_{F} = 8 \; A; V_{R} = 400 \; V; dI_{F}/dt = 500 \; A/\mus; \\ T_{j} = 25 \; ^{\circ}C; \; see \; \underline{Figure 5} \end{array}$ | - | 20 | - | ns |
| I _{RM} | peak reverse recovery current | $ I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s}; $ | - | 9.5 | 12 | А |
| | | I_F = 8 A; V_R = 400 V; dI_F/dt = 50 A/µs; T_j = 125 °C | - | 1.5 | 5.5 | А |
| V_{FR} | forward recovery voltage | I _F = 10 A; dI _F /dt = 100 A/μs; T _j = 25 °C; see <u>Figure 6</u> | - | 8 | 10 | V |
| | voltage | see <u>Figure 6</u> | | | | |

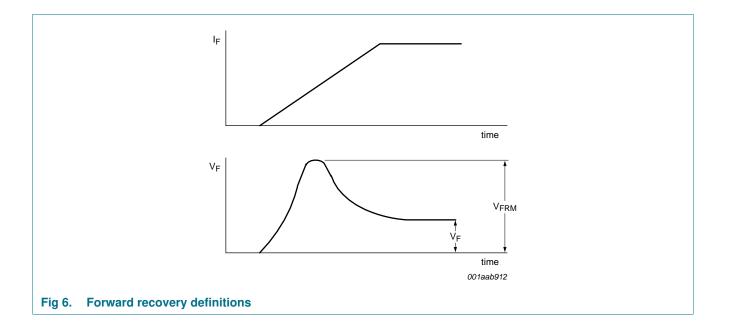




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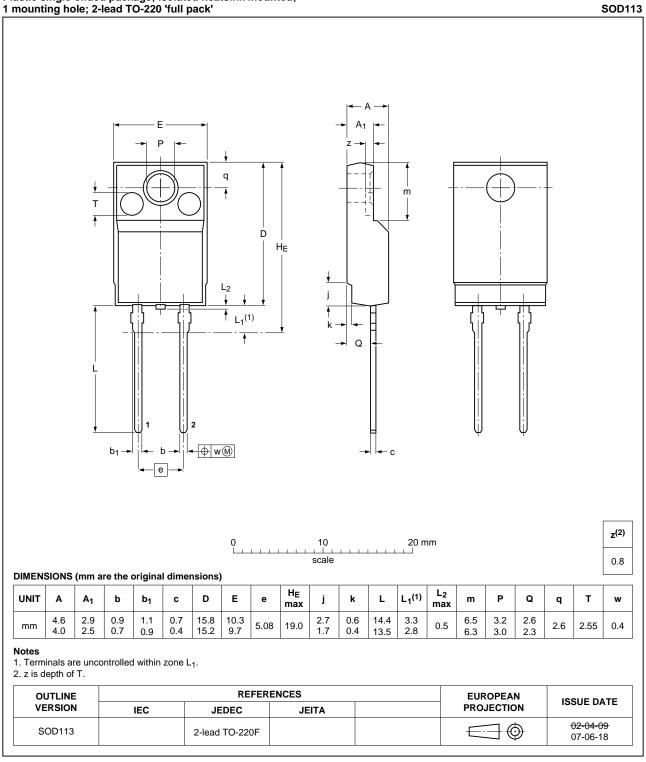


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Package outline 8.



Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

Fig 7. Package outline SOD113 (TO-220F)

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9. Revision history

| Table 8. Revision | Revision history | | | | | | |
|-------------------|------------------|--------------------|---------------|------------|--|--|--|
| Document ID | Release date | Data sheet status | Change notice | Supersedes | | | |
| BYC8DX-600 v.1 | 20101227 | Product data sheet | - | - | | | |

10. Legal information

10.1 Data sheet status

| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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